









CEB07N65

650V Δ 1.1Ω Δ 7A Δ Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

TO263 (D2PAK) package ▲ MSL 3

Super high dense cell density for extremely low R_{DS(ON)}

High power and current handling capability

MAXIMUM RATINGS

Parameter (T _c = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	650V
Gate-Source Voltage	V_{GS}	±30V
Continuous Drain Current at T _C = 25°C	l _D	7A
Pulsed Drain Current Note 1	I _{DM} Note 5	28A
Maximum Power Dissipation at T _C = 25°C	P _D	166W
Power Dissipation Derating above 25°C	ΔP_D	1.3W/°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

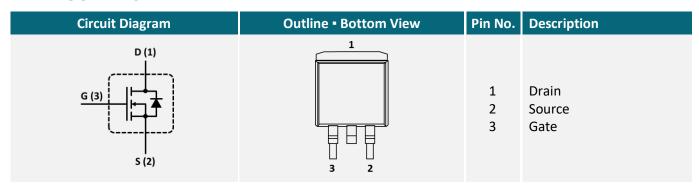
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	0.75°C/W
Thermal Resistance, Junction-to-Ambient	R _{TH_JA}	62.5°C/W

APPLICATIONS

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
₹ /•			PFC	*		

PIN DESCRIPTION





ELECTRICAL CHARACTERISTICS ▲ T_C = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250\mu A$	BV_DSS	650			V
Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V$	I _{DSS}			25	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	I_{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -30V, V_{DS} = 0V$	I_{GSSR}			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	$V_{GS(th)}$	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 5.5A$	R _{DS(ON)}		1.1	1.3	Ω
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		1310		pF
Output Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		150		pF
Reverse Transfer Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1MHz$	C_{RSS}		15		pF
Switching Characteristics Note 3						
Turn-On Delay Time	$V_{DD} = 300V$, $V_{GS} = 10V$, $I_D = 7A$, $R_{G(ext)} = 25\Omega$	t _{D(ON)}		34		ns
Turn-On Rise Time	V_{DD} = 300V, V_{GS} = 10V, I_D = 7A, $R_{G(ext)}$ = 25 Ω	t_R		19		ns
Turn-Off Delay Time	V_{DD} = 300V, V_{GS} = 10V, I_D = 7A, $R_{G(ext)}$ = 25 Ω	t _{D(OFF)}		90		ns
Turn-Off Fall Time	V_{DD} = 300V, V_{GS} = 10V, I_D = 7A, $R_{G(ext)}$ = 25 Ω	t_{\scriptscriptstyleF}		22		ns
Total Gate Charge	$V_{DS} = 480V$, $V_{GS} = 10V$, $I_{D} = 7A$	Q_{G}		32		nC
Gate Source Charge	$V_{DS} = 480V$, $V_{GS} = 10V$, $I_{D} = 7A$	Q_{GS}		6		nC
Gate Drain Charge	$V_{DS} = 480V$, $V_{GS} = 10V$, $I_D = 7A$	Q_{GD}		13		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		Is			7	Α
Drain-Source Diode Forward Voltage Note 2	$V_{GS} = 0V$, $I_S = 5A$	V_{SD}			1.4	V

Notes

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: Limited only by maximum temperature allowed.
- 5: Pulse width limited by safe operating area.



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



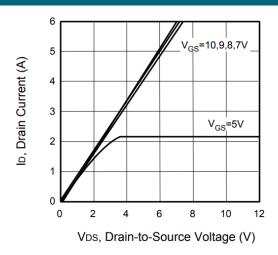


Fig. 2 • Transfer Characteristics

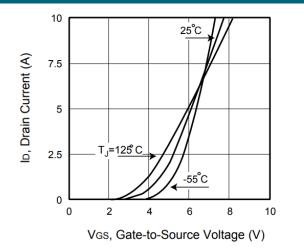


Fig. 3 • Capacitance

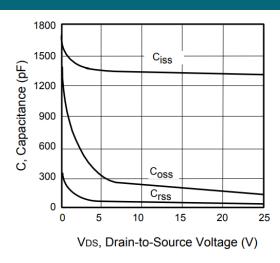


Fig. 4 • On-Resistance Variation with Temperature

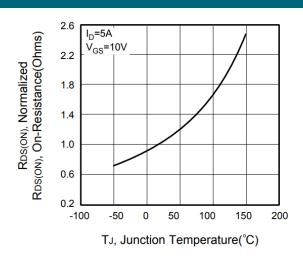


Fig. 5 • Gate Threshold Variation with Temperature

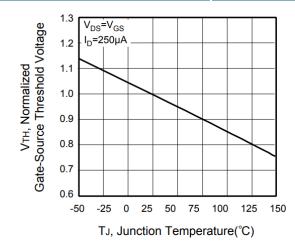
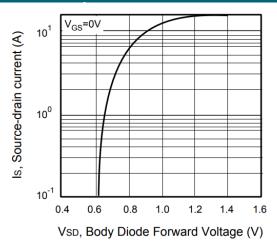


Fig. 6 • Body Diode Forward Voltage Variation with Source Current





REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

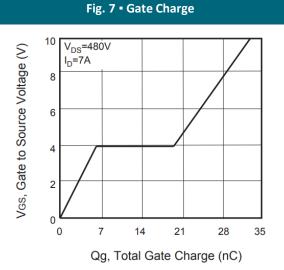


Fig. 8 • Maximum Safe Operating Area

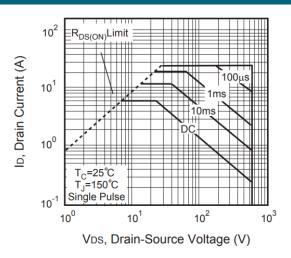
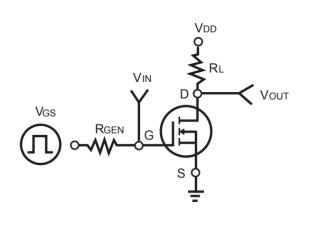


Fig. 9 • Switching Test Circuit

Fig. 10 • Switching Waveforms



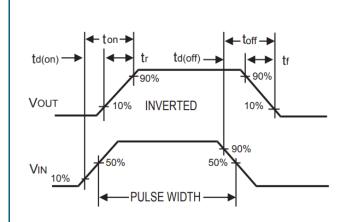
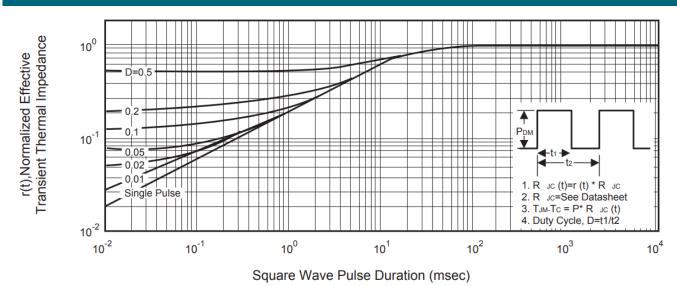


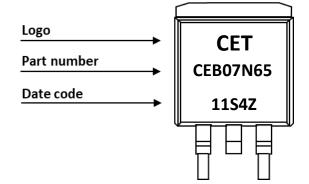
Fig. 11 - Normalized Thermal Transient Impedance Curve



MGT ▲ Manufacturer Group of Technolog

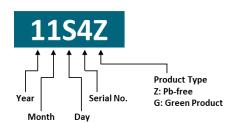


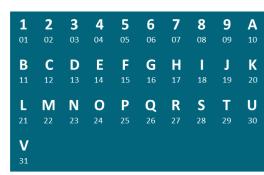
PART MARKING



DATE CODE

Example: 11S4Z



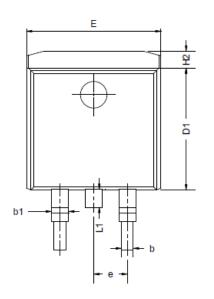


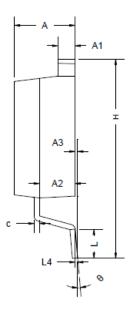
Coding list for "Day"

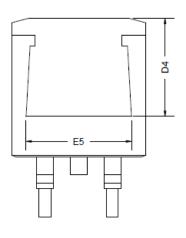


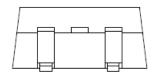


PACKAGE OUTLINE









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
Α	4.37	4.57	4.77	
A1	1.22	1.27	1.42	
A2	2.49	2.69	2.89	
А3	0.00	0.13	0.25	
b	0.70	0.81	0.96	
b1	1.17	1.27	1.47	
С	0.30	0.38	0.53	
D1	8.50	8.70	8.90	
D4	6.60	-	-	

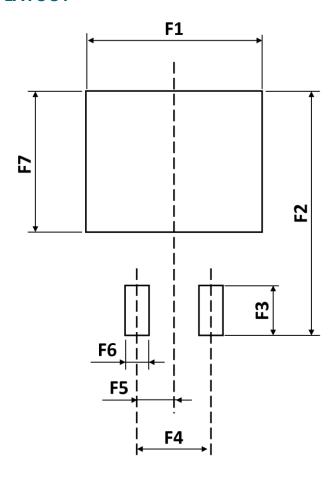
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)			
Е	9.86	10.16	10.36			
E5	7.06	-	-			
е	2.54 BSC					
Н	14.70	15.10	15.50			
H2	1.07	1.27	1.47			
L	2.00	2.30	2.60			
L1	1.40	1.55	1.70			
L4	0.25 BSC					
θ	0°	5°	9°			

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CFB07N65	TO263 (D2PAK)	Reel	800pcs	800ncs	6.400ncs



RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
F1	-	12.20	-	
F2	-	16.90	-	
F3	-	2.54	-	
F4	-	5.08	-	

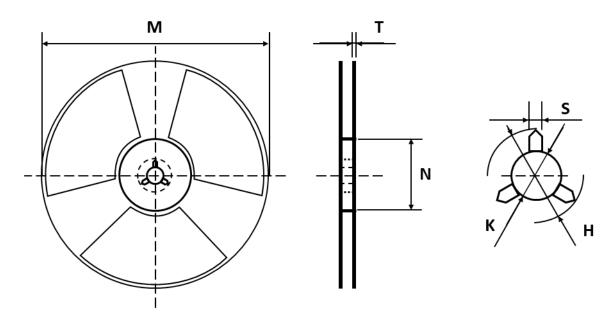
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	2.54	-
F6	-	1.60	-
F7	-	9.75	-

Notes:

- 1. The suggested land pattern dimensions have been provided for reference only.
- 2. For further information, please reference document IPC-7351A.

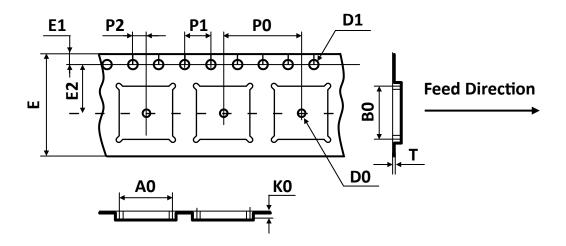


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	T	Н	K	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm	Ø330	+2.00	+0.50	±0.20	±0.50	+0.50	+0.50
		±2.00 ±0.50	±0.20	±0.50	-0.20	-0.20	

TAPE DIMENSIONS ▲ All dimensions in mm

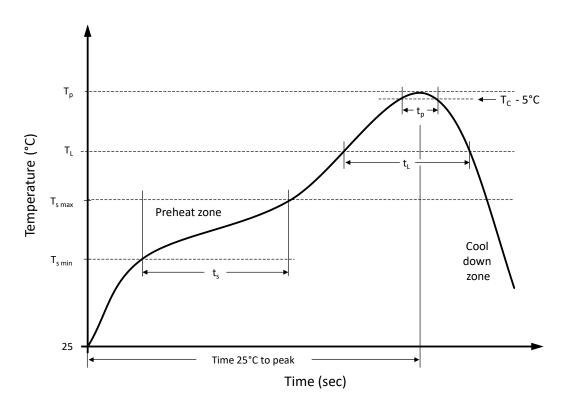


Package	A0	В0	КО	D0	D1	E	E1	E2	Р0	P1	P2	T
TO263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D ² PAK)	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t_L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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